Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S24 6	2	(sige or silicon near2 germanium) near15 (transistor) near10 photovolt\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/02 15:17
S24 8	2	polycrystal\$6 near15 (sige or silicon near2 germanium) same (transistor) near10 photovolt\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/02 15:36
S24 7	23	(sige or silicon near2 germanium) same (transistor) near10 photovolt\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/02 15:36
S25 0	2	polycrystal\$6 near15 (sige or silicon near2 germanium) and (sige or silicon near2 germanium) near15 (transistor) and (sige or silicon near2 germanium) near10 photovolt\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/02 15:37
S24 9	2	polycrystal\$6 near15 (sige or silicon near2 germanium) and (sige or silicon near2 germanium) same (transistor) near10 photovolt\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/02 15:37
S25 1	6	(sige or silicon near2 germanium) near15 (transistor) and (sige or silicon near2 germanium) near10 photovolt\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/02 15:38
S25 2	10	photovolt\$6 near15 gate near4 insulat\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 13:55
S25 3	26	(photovolt\$6 or solar near2 cell) near15 gate near4 insulat\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 13:58
S25 4	109	silicon near5 (sige) near15 gate near2 insulat\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 14:03

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S25 5	0	(sige or silicon near2 germanium) near15 gate near2 insulat\$7 near15 (solar near2 cell or photovolt\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 14:04
S25 7	574	polycrystal\$5 near10 (sige or silicon near2 germanium) near16 (oxide or insulat\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 14:37
S25 6	3	(sige or silicon near2 germanium) near15 gate near2 insulat\$7 and (solar near2 cell or photovolt\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 14:37
S26 0	0	polycrystal\$5 near10 (sige or silicon near2 germanium) near16 (oxide or insulat\$6) near15 si near15 ("and")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 14:38
S25 9	0	polycrystal\$5 near10 (sige or silicon near2 germanium) near16 (oxide or insulat\$6) near15 si near5 ("and")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 14:38
S25 8	179	polycrystal\$5 near10 (sige or silicon near2 germanium) near16 (oxide or insulat\$6) near15 si	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 14:38
S26 1	14	polycrystal\$5 near10 (sige or silicon near2 germanium) near16 (oxide or insulat\$6) near15 si and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 15:11
S26 2	631	(si or silicon) near12 (sige or silicon near2 germanium) near15 layered	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 15:22
S26 4	11	(si or silicon) near12 (sige or silicon near2 germanium) near15 layered near15 (polycrystal\$6) near15 insulat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 15:23
S26 3	37	(si or silicon) near12 (sige or silicon near2 germanium) near15 layered near15 (polycrystal\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 15:30

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S26 7	375	(solar near2 cell or photovolt\$6) near15 insulat\$6 and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 15:31
S26 6	2	(solar near2 cell or photovolt\$6) near15 insulat\$6 near15 (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 15:31
S26 5	3847	(solar near2 cell or photovolt\$6) near15 insulat\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 15:31
S26 9	149	(solar near2 cell or photovolt\$6) near15 insulat\$5 near2 layer and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 15:33
S26 8	118	(solar near2 cell or photovolt\$6) near15 insulator and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 15:33
S27 0	95	S269 and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:18
S27 1	2	"20020043660"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:20
S27 2	7296	(tft or thin near2 film near2 transistor) near15 (polysi or polycrystal\$6 near2 (si or silicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:21
S27 3	905	(tft or thin near2 film near2 transistor) near15 (polysi or polycrystal\$6 near2 (si or silicon)) and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:31
S27 4	57	(tft or thin near2 film near2 transistor) near15 (polysi or polycrystal\$6 near2 (si or silicon)) near16 (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:32

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S27 6	16	(tft or thin near2 film near2 transistor) near15 (polysi or polycrystal\$6 near2 (si or silicon)) near16 (sige or silicon near2 germanium) and @py<"2002" and gate near2 insulat\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:33
S27 5	27	(tft or thin near2 film near2 transistor) near15 (polysi or polycrystal\$6 near2 (si or silicon)) near16 (sige or silicon near2 germanium) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:33
S27 7	58	(US-20010002324-\$ or US-20030022471-\$ or US-20020113268-\$ or US-20020043660-\$ or US-20020019101-\$).did. or (US-5616932-\$ or US-6482684-\$ or US-4771015-\$ or US-5753541-\$ or US-5726487-\$ or US-4766091-\$ or US-5712191-\$ or US-6066547-\$ or US-6130981-\$ or US-6118151-\$ or US-6277679-\$ or US-6204156-\$ or US-5766989-\$ or US-5758520-\$ or US-602744-\$ or US-4757030-\$ or US-602744-\$ or US-4757030-\$ or US-6423585-\$ or US-4975387-\$ or US-6225197-\$ or US-6423585-\$ or US-4309225-\$ or US-6225197-\$ or US-6495404-\$ or US-5923966-\$ or US-6495404-\$ or US-5923966-\$ or US-5834071-\$ or US-6461945-\$ or US-5834071-\$ or US-6461945-\$ or US-5932118-\$ or US-5767003-\$ or US-5932118-\$ or US-5767003-\$ or US-5839949-\$ or US-5767003-\$ or US-5893949-\$ or US-5767003-\$ or US-5893949-\$ or US-5767003-\$ or US-5821158-\$ or US-592365-\$ or US-5821158-\$ or US-5767003-\$ or US-5821158-\$ or US-5797998-\$).did. or (WO-9931719-\$).did. or (US-68268587-\$ or US-5797998-\$).did. or (US-68268587-\$ or US-5797998-\$).did. or (US-68268587-\$ or US-5821158-\$ or US-59129859-\$).did. or (US-68268587-\$).did. or (US-68268587-\$).did. or (US-68268587-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/10/11 16:36
S27 9	2	multibandgap near4 photovolt\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:47
S27 8	26	S277 and gate near3 insulat\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:47

S28 0	6	multi\$1band\$1gap near4 photovolt\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:48
S28 2	0	(polysilicon or sige) near15 (tft) near15 photovolt\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:49
S28 1	70	photovolt\$5.ab. and gate near2 insulat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:49
S28 3	3	(polysilicon or sige) near15 (thin near2 film near2 transistor) near15 photovolt\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:53
S28 4	24	amorphous near2 (sige or silicon near2 germanium) near15 laser near15 (crystalliz\$5 or polycrystal\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 16:54
S28 5	23	(sige near12 si) near15 (Tft or thin near2 film near2 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 21:18
S28 6	0	"5461250".pn. and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 23:15
S28 7	1	"5461250".pn. and recrystal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 23:18
S28 8	1	"5461250".pn. and amorphous\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 23:22
S28 9	10	(silicon near2 germanium sige) near4 (tft or thin near2 film near2 transistor) same (recrystal\$5 or laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/11 23:25

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S29 2		(tft or thin near2 film near2 transistor) and (sige\$1si or si\$1sige) near15 amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/12 09:40
S29 3	0	(tft or thin near2 film near2 transistor) and (sige\$1si or si\$1sige) near15 laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/12 09:41
S29 1	102	(tft or thin near2 film near2 transistor) and (sige\$1si or si\$1sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/12 09:41
S29 5	118	(silicon near2 germanium sige) near4 (tft or thin near2 film near2 transistor) and amorphous near15 polycrystall\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/12 09:42
S29 4	3	(tft or thin near2 film near2 transistor) and (sige\$1si or si\$1sige) near10 polycrystal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/12 09:42
S29 0	12	(silicon near2 germanium sige) near4 (tft or thin near2 film near2 transistor) and amorphous near15 polycrystall\$6 near10 laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/12 09:42
S29 6	23	(silicon near2 germanium sige) near4 (tft or thin near2 film near2 transistor) and amorphous near15 polycrystall\$6 and @py<"2003"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/12 09:43
S29 8	239	amorphous near15 recrystal\$6 near15 laser near15 polycrystal\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/13 11:31
S29 7	25	(sige or silicon near2 germanium) near15 amorphous near15 recrystal\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/13 11:31
S29 9	109	amorphous near15 recrystal\$6 near15 laser near15 polycrystal\$7 and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/13 11:32

S30 0	10	amorphous near15 recrystal\$6 near15 laser near15 polycrystal\$7 same (tft or thin near2 film near2 transistor) and @py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/13 11:33
S30 2	3	"6482684".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 01:10
S30 1	26	("4569894" "5241214" "5461250" "5591653" "5619044" "5712191" "5888858" "5904567" "6180439" "6287944" "6444390" "6703265" "6939755").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/15 01:10